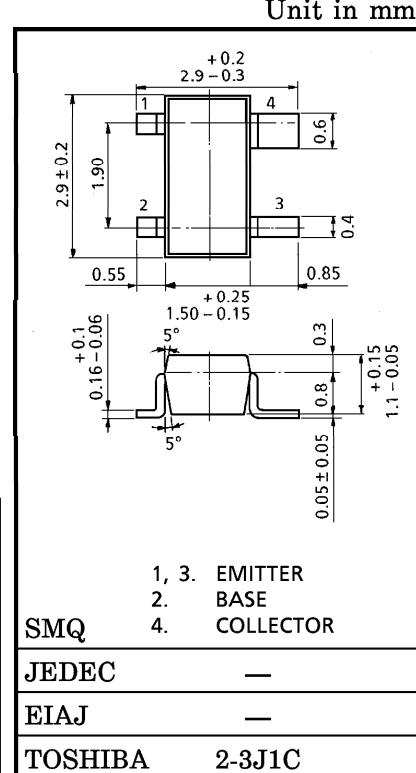


TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

MT4S06

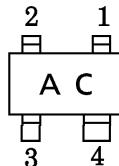
VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

- Low Noise Figure : $NF = 1.6 \text{ dB}$
($V_{CE} = 3 \text{ V}$, $I_C = 3 \text{ mA}$, $f = 2 \text{ GHz}$)
- High Gain : $|S_{21e}|^2 = 11.5 \text{ dB}$
($V_{CE} = 3 \text{ V}$, $I_C = 7 \text{ mA}$, $f = 2 \text{ GHz}$)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	10	V
Collector-Emitter Voltage	V_{CEO}	5	V
Emitter-Base Voltage	V_{EBO}	1.5	V
Base Current	I_B	15	mA
Collector Current	I_C	7	mA
Collector Power Dissipation	P_C	60	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55 \sim 125$	$^\circ\text{C}$

MARKING



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MICROWAVE CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Transition Frequency	f _T	V _{CE} = 3 V, I _C = 5 mA	7	10	—	GHz
Insertion Gain	S _{21e} ² (1)	V _{CE} = 1 V, I _C = 5 mA, f = 2 GHz	—	10.5	—	dB
	S _{21e} ² (2)	V _{CE} = 3 V, I _C = 7 mA, f = 2 GHz	8.5	11.5	—	
Noise Figure	NF (1)	V _{CE} = 1 V, I _C = 3 mA, f = 2 GHz	—	1.7	3	dB
	NF (2)	V _{CE} = 3 V, I _C = 3 mA, f = 2 GHz	—	1.6	3	

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CB0}	V _{CB} = 5 V, I _E = 0	—	—	0.1	μA
Emitter Cut-off Current	I _{EB0}	V _{EB} = 1 V, I _C = 0	—	—	1	μA
DC Current Gain	h _{FE}	V _{CE} = 1 V, I _C = 5 mA	70	—	140	—
Reverse Transfer Capacitance	C _{re}	V _{CB} = 1 V, I _E = 0, f = 1 MHz (Note)	—	0.23	0.7	pF

(Note) : C_{re} is measured by 3 terminal method with capacitance bridge.

CAUTION

This device electrostatic sensitivity. Please handle with caution.